



Patents, Trademarks and Related Matters

Killworth, Gottman, Hagan &amp; Schaeff, L.L.P.

One Dayton Centre  
One South Main Street, Suite 500  
Dayton, Ohio 45402-2023937.223.2050  
Fax | 937.223.0724  
E-mail | kghs@kghs.com  
www.KGHS.com**FACSIMILE TRANSMISSION**To: O. Nadav, Art Unit 2811  
Company: Patent and Trademark Office  
Fax no: 703-308-7722From: William A. Jividen, Esq.  
Our ref: MIO 0054 PA

Date: March 5, 2003

No. pages: 9 (including cover)

Trans. no:

**FAX RECEIVED**

MAR 5 2003

TECHNOLOGY CENTER 2800

ORIGINAL WILL FOLLOW BY REGULAR MAIL

X ORIGINAL WILL NOT FOLLOW

**REMARKS:**IF YOU HAVE ANY PROBLEMS RECEIVING THIS TELECOPY MESSAGE, PLEASE  
CALL KERRIE CELA AT (937) 223-2050 AS SOON AS POSSIBLE. THANK YOU.

OFFICIAL

OFFICIAL

OFFICIAL

Application of

Applicants : Chandra V. Mouli and Ceredig Roberts

Serial No. : 09/648,044

Filed : August 25, 2000

Confirm No. : 6800

Title : METHOD AND DEVICE TO REDUCE GATE-INDUCED DRAIN  
LEAKAGE (GIDL) CURRENT IN THIN GATE OXIDE MOSFETs

Docket No. : MIO 0054 PA

Examiner : O. Nadav

Art Unit : 2811

03/05/03 18:07

937 223 0724

KILLWORTH ET AL

002/009

OFFICIAL

OFFICIAL

OFFICIAL

Response Under 37 CFR 1.116  
Expedited Procedure  
Examining Gr up 2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicants : Chandra V. Mouli and Ceredig Roberts  
Serial No. : 09/648,044  
Filed : August 25, 2000  
Confirm No. : 6800  
Title : **METHOD AND DEVICE TO REDUCE GATE-INDUCED DRAIN  
LEAKAGE (GIDL) CURRENT IN THIN GATE OXIDE MOSFETs**  
Docket No. : MIO 0054 PA  
Examiner : O. Nadav  
Art Unit : 2811

FAX RECEIVED

MAR 5 2003

TECHNOLOGY CENTER

Assistant Commissioner for Patents  
Washington, D.C. 20231

CERTIFICATE OF FACSIMILE TRANSMISSION  
I hereby certify that this correspondence is being  
facsimile transmitted to the Patent and Trademark  
Office ((703) 308-7722) on March 5, 2003.

William A. Jviden

42.695  
Reg. No.

Sir:

**AMENDMENT AFTER FINAL REJECTION**

This paper is being filed in response to the office action made final and dated February 24, 2003 in the identified application. Reconsideration and reexamination are respectfully requested in light of the amendments and remarks below.

In the Claims

Please note that the entire set of presently pending claims has been reproduced below for the convenience of the Examiner. Amended claims are indicated as such in the parenthetical following each claim number.

1. (Currently Amended) A circuit structure comprising:

- a semiconductor layer;
- an oxide layer formed on said semiconductor layer;
- a gate structure formed on said oxide layer having first and second leading edges; and